1,048,576 WORD ×4 BIT DYNAMIC RAM

### **PRELIMINARY**

#### **DESCRIPTION**

The TC514400APL/AJL/ASJL/AZL is the new generation dynamic RAM organized 1,048,576 words by 4 bits. The TC514400APL/AJL/ASJL/AZL utilizes TOSHIBA's CMOS Silicon gate process technology as well as advanced circuit techniques to provide wide operating margins, both internally and to the system user. Multiplexed address inputs permit the TC514400APL/AJL/ASJL/AZL to be packaged in a standard 20 pin plastic DIP, 26/20 pin plastic SOJ (300/350mil) and 20 pin plastic ZIP. The package size provides high system bit densities and is compatible with widely available automated testing and insertion equipment. System oriented features include single power supply of 5V±10% tolerance, direct interfacing capability with high performance logic families such as Schottky TTL.

#### **FEATURES**

- 1,048,576 word by 4 bit organization
- · Fast access time and cycle time

trac		TC514400APUAJUASJUAZL - 70/ - 80/ - 10					
	RAS Access Time	70ns	80ns	100ns			
taa	Column Address Access Time	35ns	40ns	50ns			
t <sub>CAC</sub>	CAS Access Time	20ns	20ns	25ns			
t <sub>RC</sub>	Cycle Time	130ns	150ns	180ns			
tpc	Fast Page Mode Cycle Time	45ns	50ns	60ns			

 Single power supply of 5V±10% with a built-in VBB generator

#### PIN NAMES

A0~A9	Address Inputs	ŌĒ	Output Enable
RAS	Row Address Strobe	1/01~1/04	Data Input/Output
CAS	Column Address Strobe	Vcc	Power ( + 5V)
WRITE	Read/Write Input	Vss	Ground

Low Power

550mW MAX. Operating (TC514400APL/AJL/ASJL/AZL-70)

468mW MAX. Operating

(TC514400APL/AJL/ASJL/AZL-80)

413mW MAX. Operating

(TC514400APL/AJL/ASJL/AZL-10)

1.1mW MAX. Standby

Outputs unlatched at cycle end allows twodimensional chip selection

 Read-Modify-Write, CAS before RAS refresh, RAS-only refresh, Hidden refresh, and Fast Page Mode and Test Mode capability

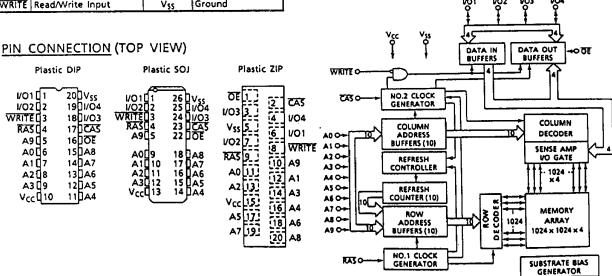
All inputs and outputs TTL compatible

1024 refresh cycles/128ms

Package TČ514400APL : DIP20-P-300C

TC514400AJL: SOJ26-P-350 TC514400ASJL: SOJ26-P-300A TC514400AZL: ZIP20-P-400A

BLOCK DIAGRAM



#### **ABSOLUTE MAXIMUM RATINGS**

Mati	SYMBOL	RATING	UNITS	NOTES
Input Voltage	VIN	-1~7	٧	1
Output Voltage	Vout	-1~7	٧	1
Power Supply Voltage	Vcc	-1~7	v	1
Operating Temperature	TOPR	0~70	•c	1
Storage Temperature	T <sub>STG</sub>	- 55~150	•c	1
Soldering Temperature - Time	TSOLDER	260 - 10	*C · sec	1
Power Dissipation	Po	700	mW	1
Short Circuit Output Current	lout	50	mA	1

### RECOMMENDED DC OPERATING CONDITIONS (Ta = $0 \sim 70$ °c)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT	NOTES
Vcc	Supply Voltage	4.5	5.0	5.5	٧	2
V <sub>IH</sub>	Input High Voltage	2.4	-	6.5	v	2
VIL	Input Low Voltage	- 1.0	-	0.8	v	7

### DC ELECTRICAL CHARACTERISTICS ( $V_{CC} = 5V \pm 10\%$ , $Ta = 0 \sim 70$ °c)

SYMBOL	PARAMETER		MIN.	MAX.	UNITS	NOTES
	OPERATING CURRENT	TC514400APL/AĴUASJUAZL-70	_	100		3, 4
lcc1	Average Power Supply Operating Current	TC514400APL/AJL/ASJL/AZL-80	-	85	mA	5
•••	(RAS, CAS, Address Cycling: t <sub>RC</sub> = t <sub>RC</sub> MIN.)	TC514400APUAJUASJUAZL-10	<u> </u>	75	mA mA pA pA pA pA pA pA	3
1 <sub>CC2</sub>	STANDBY CURRENT Power Supply Standby Current (RAS = CAS = V <sub>IH</sub> )		-	2	mA	
	RAS ONLY REFRESH CURRENT	TC514400APWAJWASJWAZL-70		100		
Іссз	Average Power Supply Current, RAS Only Mode	TC514400APL/AJL/ASJL/AZL-80		85	mA	3, 5
	(RAS Cycling, CAS = VIH: tRC = tRC MIN.)	TC514400APUAJUASJUAZL-10	-	75	]	
	FAST PAGE MODE CURRENT	TCS14400APL/AJL/ASJL/AZL-70	-	70		3,
	Average Power Supply Current, Fast Page Mode	TC514400APL/AJL/ASJL/AZL-80	-	60	mA	
I <sub>CC4</sub>	(RAS = VIL, CAS, Address Cycling: tpc = tpc MiN.)	TC514400APUAJUASJUAZL-10	-	55		5
I <sub>CCS</sub>	STANDBY CURRENT Power Supply Standby Current (RAS = CAS = V <sub>CC</sub> - 0.2V)	ower Supply Standby Current				
	CAS BEFORE RAS REFRESH CURRENT Average Power Supply Current, CAS Before RAS	TCS14400APWAJWASJWAZL-70		100	mA	
l <sub>CC6</sub>		TCS14400APUAJUASJUAZL-80	_	85		3,
	Mode (RAS, CAS Cycling: t <sub>RC</sub> = t <sub>RC</sub> MIN.)					
l <sub>CC7</sub>	Battery Back Up Current  Average Power Supply Current, Battery Back Up (CAS = CAS Before RAS Cycling or 0.2V, OE = Vcc 0.2V, A0~9 = Vcc - 0.2V or 0.2V, VO1~4 = Vcc - 0.2V or OPEN: t <sub>RC</sub> = 125µs, t <sub>RAS</sub> = 300ns ~1µs)	-0.2V, WRITE = VCC-	-	400	μΑ	3,
Jeo S	Battery Back Up Current  Average Power Supply Current, Battery Back Up  ( $\overline{CAS} = \overline{CAS}$ Before $\overline{RAS}$ Cycling or 0.2V, $\overline{OE} = V_{CC}$ 0.2V, $A0 \sim 9 = V_{CC} - 0.2$ V or 0.2V, $VO1 \sim 4 = V_{CC} - 0.2$ V or 0.2V or 0.2V or 0.2V. $VO1 \sim 4 = V_{CC} - 0.2$ V or 0.2V or 0.2V. $VO1 \sim 4 = V_{CC} - 0.2$ V or 0.2V or 0.2V. $VO1 \sim 4 = V_{CC} - 0.2$ V or 0.2V or 0.2V. $VO1 \sim 4 = V_{CC} - 0.2$ V or 0.2V.	- 0.2V, WRITE = V <sub>CC</sub> - 0.2V,	-	300	μΑ	3,
lı (L)	INPUT LEAKAGE CURRENT Input Leakage Current, any input (0V≤V <sub>IN</sub> ≤6.5V, All Other Pins Not Under Test=	■ 0V)	- 10	10	ДД	
lo (L)	OUTPUT LEAKAGE CURRENT (O <sub>OUT</sub> is disabled, 0V≤V <sub>OUT</sub> ≤5.5V)	- 10	10	μΑ		
V <sub>OH</sub>	OUTPUT LEVEL Output "H" Level Voltage (I <sub>OUT</sub> = -5mA)		2.4	_	v	
Vol	OUTPUT LEVEL Output "L" Level Voltage (I <sub>OUT</sub> = 4.2mA)		-	0.4	v	

### ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

 $(V_{CC} = 5V \pm 10\%, Ta = 0 \sim 70^{\circ}c)$  (Notes 7, 8, 9)

SYMBOL	PARAMETER		4400APL/ SJUAZL-70	TC514400APU AJUASJUAZL-80		TC514400APL/ AJL/ASJL/AZL-10		UNIT	NOTES
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		110123
t <sub>RC</sub>	Random Read or Write Cycle Time	130	_	150		180	-	ns	i
t <sub>RMW</sub>	Read-Modify-Write Cycle Time	185	-	205	-	245	-	ns	
tpc	Fast Page Mode Cycle Time	45	-	50		60	_	ns	
t <sub>PRMW</sub>	Fast Page Mode Read-Modify-Write . Cycle Time	100	-	105	-	125	-	ns	
t <sub>RAC</sub>	Access Time from RAS	-	70	-	80	,	100	ns	10,15 16
t <sub>CAC</sub>	Access Time from CAS	T - T	20	-	20	_	25	ns	10,15
t <sub>AA</sub>	Access Time from Column Address	- 1	35	_	40	-	50	ns	10,16
t <sub>CPA</sub>	Access Time from CAS Precharge	T - T	40	_	45	_	55	ns	10
t <sub>CLZ</sub>	CAS to output in Low-Z	0	_	0	•	0	_	ns	10
t <sub>OFF</sub>	Output Buffer Turn-off Delay	0	20	0	20	0	20	ns	11
t <sub>7</sub>	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	9
t <sub>RP</sub>	RAS Precharge Time	50	-	60	-	70		ns	
t <sub>RAS</sub>	RAS Pulse Width	70	10,000	80	10,000	100	10,000	ns	
tRASP	RAS Pulse Width (Fast Page Mode)	70	200,000	80	200,000	100	200,000	ns	
tash	RAS Hold Time	20	_	20	_	25		ns	
t <sub>RHCP</sub>	RAS Hold Time From CAS Precharge (Fast Page Mode)	40	-	45	-	55	-	ns	
<sup>t</sup> csH	CAS Hold Time	70	-	80	-	100	_	ns	
t <sub>CAS</sub>	CAS Pulse Width	20	10,000	20	10,000	25	10,000	ns	
t <sub>RCD</sub>	RAS to CAS Delay Time	20	50	20	60	25	75	ns	15
tRAD	RAS to Column Address Delay Time	15	35	15	40	20	50	ns	16
t <sub>CRP</sub>	CAS to RAS Precharge Time	5	-	5	-	5	-	ns	
t <sub>CP</sub>	CAS Precharge Time	10	-	10	-	10	_	ns	
tasr	Row Address Set-Up Time	0	-	0		0		ns	
t <sub>RAH</sub>	Row Address Hold Time	10	-	10	_	15		ns	
tasc	Column Address Set-Up Time	0	-	0		0		ns	
t <sub>CAH</sub>	Column Address Hold Time	15	-	15	_	20		ns	<del></del>
tRAL	Column Address to RAS Lead Time	35	_	40		50			
t <sub>RCS</sub>	Read Command Set-Up Time	0		0		- 30		ns ns	
t <sub>RCH</sub>	Read Command Hold Time			-		0		ns	12

### ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS (Continued)

SYMBOL	PARAMETER		400APL/ JL/AZL-70	TC514400APL/ AJL/ASJL/AZL-80		TC514400APL/ AJL/ASJL/AZL-10		UNITS	NOTES
31 MIBOL	I CHENTE I WY	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
t <sub>RRH</sub>	Read Command Hold Time referenced to RAS	0	-	0	-	0	-	ns	12
twch	Write Command Hold Time	15		15		20	-	ns	
twp	Write Command Pulse Width	15	-	15	<u>-</u> .	20	-	ns	
t <sub>RWL</sub>	Write Command to RAS Lead Time	20	-	20		25	<u></u>	ns	
tcwL	Write Command to CAS Lead Time	20	-	20		25		ns	
tos	Data Set-Up Time	0	_	0	_	0		ns	13
t <sub>DH</sub>	Data Hold Time	15		15	-	20		ns	13
t <sub>REF</sub>	Refresh Period	-	128	_	128	-	128	ms	<u> </u>
twcs	Write Command Set-UP Time	0		0		0	-	ns	14
t <sub>CWD</sub>	CAS to WRITE Delay Time	50	•	50		60		ns	14
t <sub>RWD</sub>	RAS to WRITE Delay Time	100	-	110	-	135		ns	14
tawo	Column Address to WRITE Delay Time	65	-	70	-	85		ns	14
t <sub>CPWD</sub>	CAS Precharge to WRITE Delay Time	70	-	75	-	90		ns	14
t <sub>CSR</sub>	CAS Set-Up Time (CAS before RAS Cycle)	5	-	5	_	5	_	ns	
t <sub>CHR</sub>	CAS Hold Time (CAS before RAS Cycle)	15	_	15	-	20	_	ns	
t <sub>RPC</sub>	RAS to CAS Precharge Time	0	-	0	-	0	-	ns	ļ
t <sub>CPT</sub>	CAS Precharge Time (CAS before RAS Counter Test Cycle)	40	_	40	-	50		ns	
troh	RAS Hold Time referenced to OE	10	-	10		20	_	ns	<u> </u>
toea	OE Access Time	-	20		20	_	25	ns	<u> </u>
t <sub>OED</sub>	OE to Data Delay	20	-	20		25	-	ns	<u>                                     </u>
toez	Output buffer turn off Delay Time from OE	0	20	0	20	0	20	ns	10
toen	OE Command Hold Time	20	_	20	-	25		ns	<u> </u>
twrs	Write Command Set-Up Time (Test Mode In)	10	_	10	<b>.</b>	10	-	ns	
twtH	Write Command Hold Time (Test Mode in)	10	-	10	_	10	-	ns	
t <sub>WRP</sub>	WRITE to RAS Precharge Time (CAS before RAS Cycle)	10	-	10	-	10	_	ns	
twrH	WRITE to RAS Hold Time (CAS before RAS Cycle)	10	-	10	-	10	_	ns	



### ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS IN THE TEST MODE

SYMBOL	PARAMETER	1	TC514400APU AJUASJUAZL-70		TC514400APU AJUASJUAZL-80		TC514400APL/ AJUASJUAZL-10		NOTES
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
t <sub>RC</sub>	Random Read or Write Cycle Time	135	_	155		185	_	ns	
t <sub>RMW</sub>	Read-Modify-Write Cycle Time	190	-	210	•	250	-	ns	
t <sub>PC</sub>	Fast Page Mode Cycle Time	50	-	55	-	65	-	ns	
t <sub>RMR</sub>	Fast Page Mode Read-Modify-Write Cycle Time	190	-	210	_	250	-	ns	
t <sub>RAC</sub>	Access Time from RAS	-	75	-	85	-	105	ns	10,15 16
tcac	Access Time from CAS		25	-	25	-	30	ns	9,15
taa	Access Time from Column Address	_	40	-	45	-	55	ns	9,16
t <sub>CPA</sub>	Access Time from CAS Precharge	-	40	-	50	-	60	ns .	10
t <sub>RAS</sub>	RAS Pulse Width	75	10,000	85	10,000	105	10,000	ns	
tRASP	RAS Pulse Width (Fast Page Mode)	75	100,000	85	200,000	105	200,000	ns	
trsH	RAS Hold Time	25	-	25	-	30		ns	<del></del>
t <sub>CSH</sub>	CAS Hold Time	75	-	85	-	105	-	ns	
t <sub>RHCP</sub>	CAS Precharge to RAS Hold Time	45	-	55	_	65	_	ns	
t <sub>CAS</sub>	CAS Pulse Width	25	10,000	25	10,000	30	- 10,000	ns	
tRAL	Column Address to RAS Lead Time	40	_	45	-	55		ns	
t <sub>CWD</sub>	CAS to WRITE Delay Time	55	-	55	-	65	_	ns	14
t <sub>RWD</sub>	RAS to WRITE Delay Time	105	-	115	-	140	-	ns	14
t <sub>AWD</sub>	Column Address to WRITE Delay Time	70	-	75	-	90	-	ns	14
t <sub>CPWD</sub>	CAS Precharge to WRITE Delay Time.	75	_	80	-	95	-	ns	14
tOEA	OE Access Time from	1-1	25	-	25	_	30	ns	
<sup>t</sup> OEH	OE Command Hold Time	25		25		30		ns	

### CAPACITANCE ( $V_{CC} = 5V \pm 10\%$ , f = 1MHz, $T_0 = 0 \sim 70$ °c)

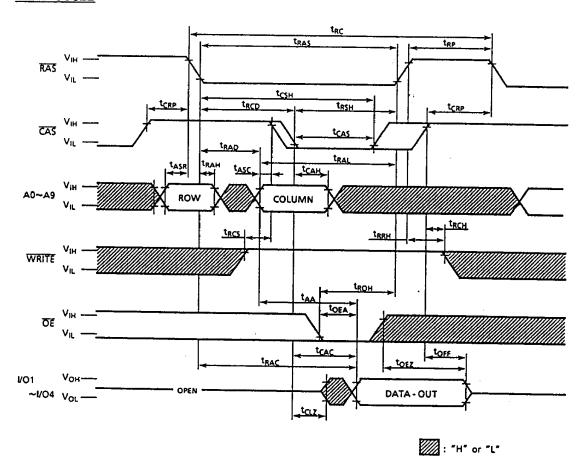
SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Cıı	Input Capacitance (A0~A9)		5	pF
C <sub>f2</sub>	Input Capacitance (RAS, CAS, WRITE, OE)		7	pr pf
co	Input/Output Capacitance (I/O1~I/O4)		7	pF

#### NOTES:

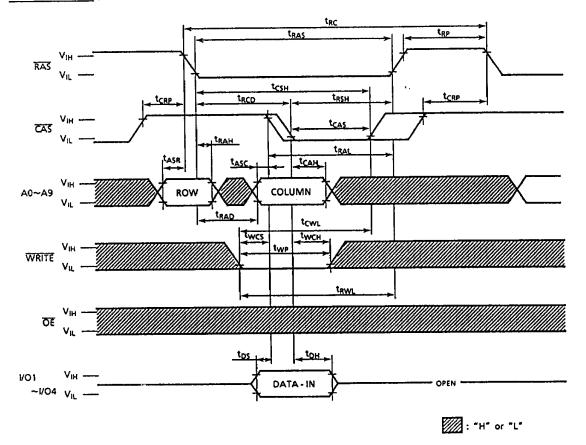
- 1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.
- 2. All voltages are referenced to VSS.
- 3. ICC1, ICC3, ICC4, ICC6, ICC7 depend on cycle rate.
- 4. ICC1, ICC4 depend on output loading. Specified values are obtained with the output open.
- 5. Column address can be changed once or less while  $\overline{RAS} = V_{IL}$  and  $\overline{CAS} = V_{IH}$ .
- 6. t<sub>RAS</sub>(max.)=1µs is only applied to refresh of battery-back up. t<sub>RAS</sub>(max.)=10µs is applied to functional operating.
- 7. An initial pause of 200µs is required after power-up followed by 8 RAS only refresh cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 CAS before RAS refresh cycles instead of 8 RAS only refresh cycles are required.
- 8. AC measurements assume t<sub>T</sub>=5ns.
- 9. VIH (min.) and VIL (max.) are reference levels for measuring timing of input signals. Also, transition times are measured between VIH and VIL.
- 10. Measured with a load equivalent to 2 TTL loads and 100pF.
- 11. toff (max.) and toez (max.) define the time at which the output achieves the open circuit condition and are not referenced to output voltage levels.
- 12. Either tRCH or tRRH must be satisfied for a read cycle.
- 13. These parameters are referenced to CAS leading edge in early write cycles and to WRITE leading edge in Read-Modify-Write cycles.
- 14. twcs, trwd, tcwd, tawd and tcpwd are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If twcs≥twcs (min.), the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) through the entire cycle; If trwd≥trwd (min.), tcwd≥tcwd (min.), tawd≥tawd (min.) and tcpwd≥tcpwd (min.) (Fast Page Mode), the cycle is a Read-Modify-Write cycle and the data out will contain data read from the selected cell: If neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
- 15. Operation within the t<sub>RCD</sub> (max.) limit insures that t<sub>RAC</sub> (max.) can be met. t<sub>RCD</sub> (max.) is specified as a reference point only: If t<sub>RCD</sub> is greater than the specified t<sub>RCD</sub> (max.) limit, then access time is controlled by t<sub>CAC</sub>.
  - 16. Operation within the t<sub>RAD</sub> (max.) limit insures that t<sub>RAC</sub> (max.) can be met. t<sub>RAD</sub> (max.) is specified as a reference point only: If t<sub>RAD</sub> is greater than the specified t<sub>RAD</sub> (max.) limit, then access time is controlled by t<sub>AA</sub>.



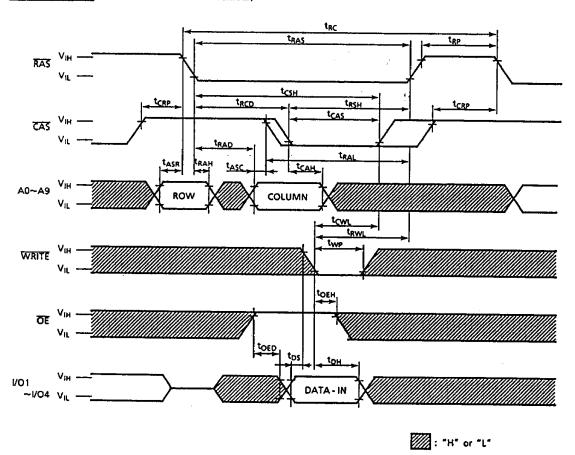
#### READ CYCLE



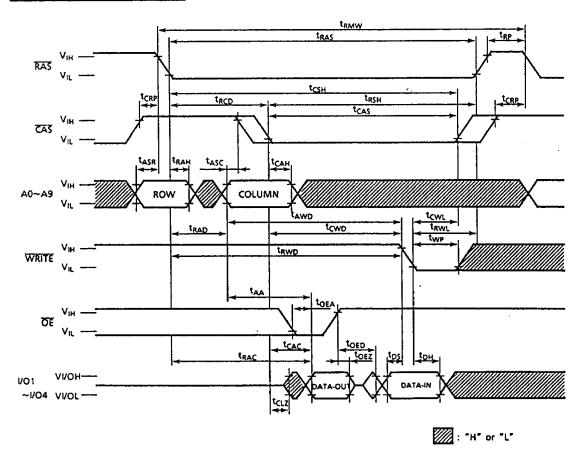
#### WRITE CYCLE (EARLY WRITE)



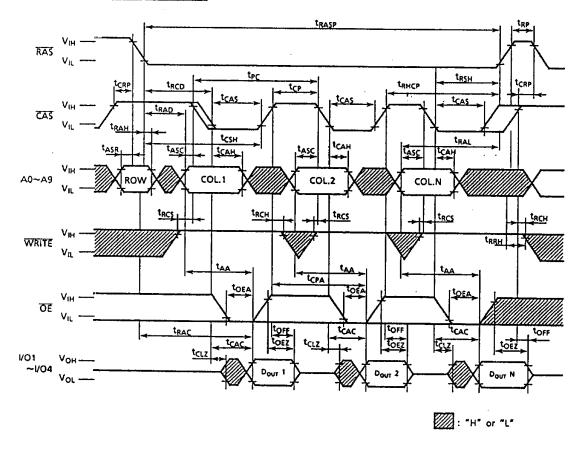
#### WRITE CYCLE (OE CONTROLLED WRITE)



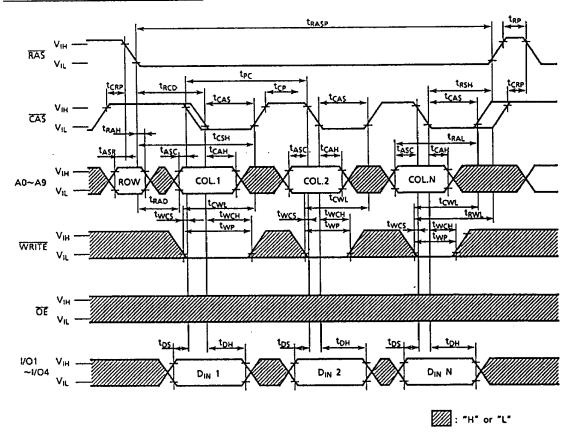
#### READ-MODIFY-WRITE CYCLE



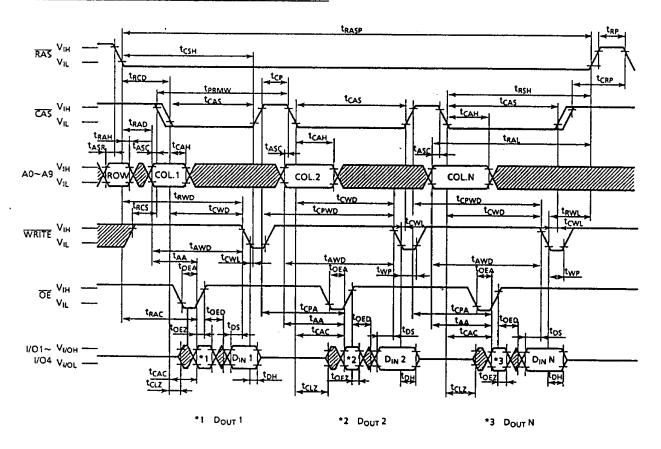
#### FAST PAGE MODE READ CYCLE



### FAST PAGE MODE WRITE CYCLE

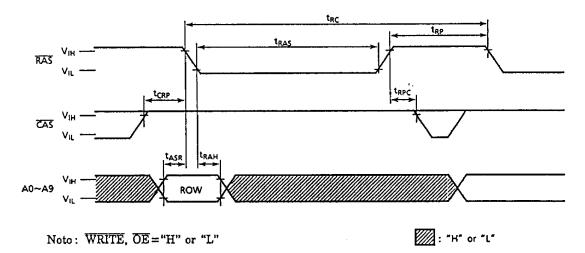


#### FAST PAGE MODE READ-MODIFY-WRITE CYCLE

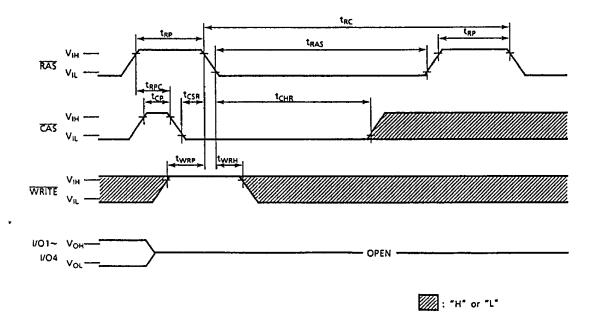


: "H" or "L"

#### RAS ONLY REFRESH CYCLE

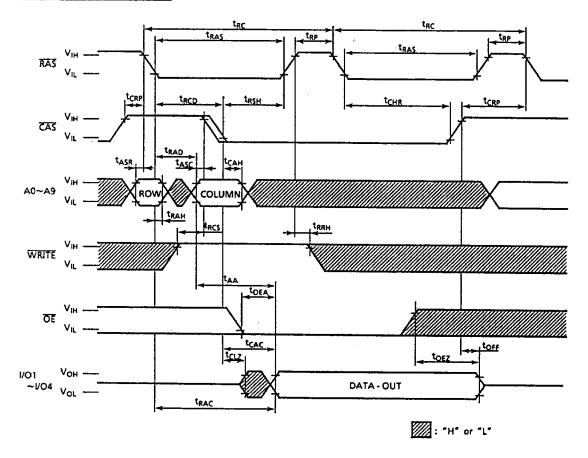


#### CAS BEFORE RAS REFRESH CYCLE

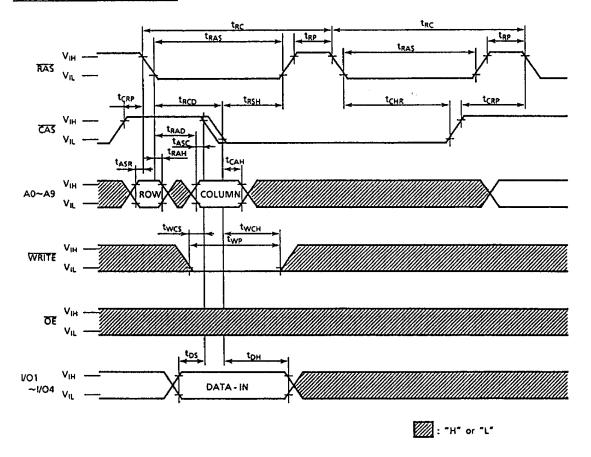


Note:  $\overline{OE}$ , A0~A9="H" or "L"

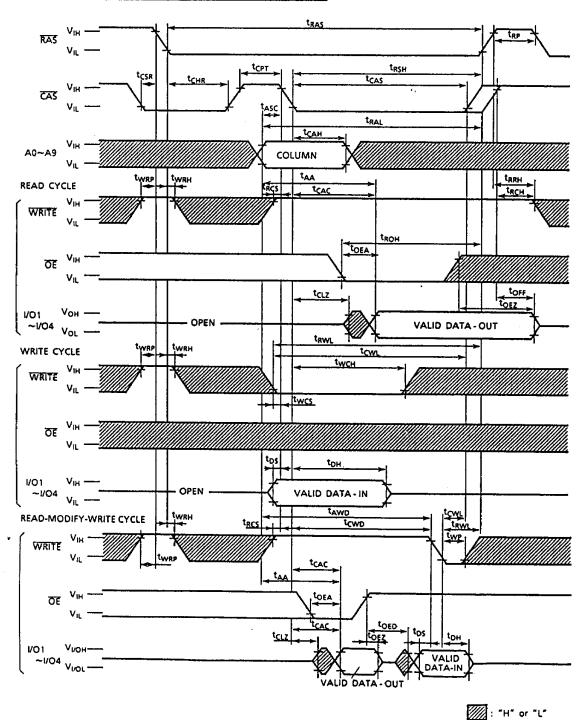
#### HIDDEN REFRESH CYCLE (READ)



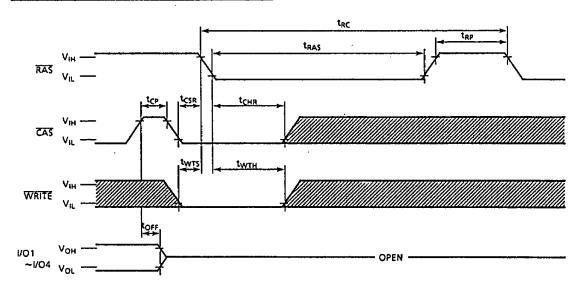
### HIDDEN REEFRESH CYCLE (WRITE)



### CAS BEFORE RAS REFRESH COUNTER TEST CYCLE



### WRITE, CAS BEFORE RAS REFRESH CYCLE



: "H" or "L"

Note: OE, A0~A9: "H" or "L"

#### **TEST MODE**

The TC514400APL/AJL/ASJL/AZL is the RAM organized 1,048,576 words by 4 bits, it is internally organized 524,288 words by 8 bits. In "Test Mode", data are written into 8 sectors in parallel and retrieved the same way. Acc is not used. If, upon reading, two bits on one I/O pin are equal (all "1"s or "0"s), the I/O pin indicates a "1".

If they were not equal, the I/O pin would indicate a "0". Fig.1 shows the block diagram of TC514400APL/AJL/ASJL/AZL. In "Test Mode", the 1M×4 DRAM can be tested as if it were a 512K×4 DRAM.

"WRITE, CAS Before RAS Refresh Cycle puts the device into "Test Mode". And "CAS Before RAS Refresh Cycle" or "RAS Only Refresh Cycle" puts it back into "Normal Mode". In the Test Mode, "WRITE, CAS Before RAS Refresh Cycle" Performs the refresh operation with the internal refresh address counter. The "Test Mode" function reduces test times (1/2 in case of N test pattern).

#### **BLOCK DIAGRAM IN THE TEST MODE**

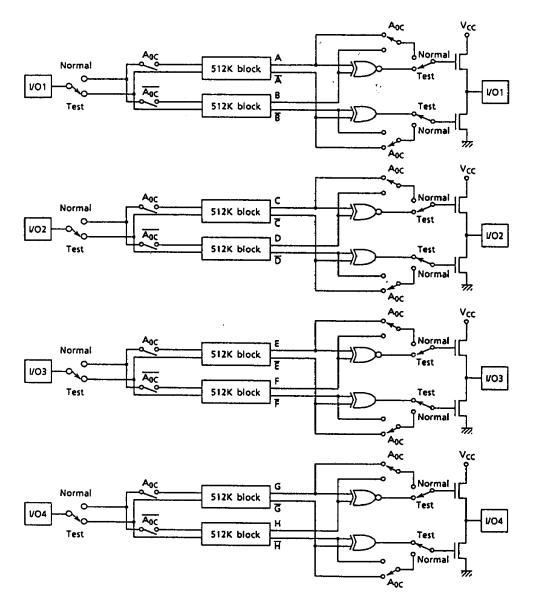


Fig. 1

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